













ESD

TVS

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GDT

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## SURFACE MOUNT SILICON

# ZENER DIODES

# PTZTE25XXB-MS

Vz: 3.6 - 36 Volts

# P<sub>D</sub>: 1.0 Watts

#### **FEATURES**

- High peak reverse power dissipation
- High reliability
- Low leakage current
- Pb / RoHS Free

#### **ECHANICAL DATA**

- Case : SMA Molded plastic
- Epoxy : UL94V-0 rate flame retardant
- Polarity : Color band denotes cathode end
- Mounting position : Any
- Weight : 0.060 gram (Approximately)

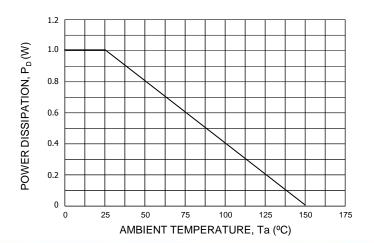
#### **Reference News**

PACKAGE OUTLINE	PIN CONFIGURATION Marking Informat		
		<b>3.6B</b> Notes :PTZTE253.6B-MS=3.6B PTZTE253.9B-MS=3.9B PTZTE254.3B-MS=4.3B And so on	
SMA(DO-214AC)			

### MAXIMUM RATINGS

Rating at 25 °C ambient temperature unless otherwise specified

Rating	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	1.0	W
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>STG</sub>	- 55 to + 150	°C



#### Fig. 1 POWER TEMPERATURE DERATING CURVE



# ELECTRICAL CHARACTERISTICS(Ta = 25 °C)

Type Marki		Zener Voltage ing Vz (V)		Test Current Іzт	Maximum Zener Impedance Zz @ Iz		Maximum Reverse Current		ypical Temperature Coefficient γz Iz		
		MIN.	TYP.	MAX.	(mA)	(Ω)	(mA)	(μΑ)	(V)	(mV/ºC)	(m <b>A</b> )
PTZTE253.6B-MS	3.6B	3.6	3.813	4.00	40	15	40	60	1.0	-2.8	40
PTZTE253.9B-MS	3.9B	3.9	4.136	4.40	40	15	40	40	1.0	-2.4	40
PTZTE254.3B-MS	4.3B	4.3	4.572	4.80	40	15	40	20	1.0	-2.1	40
PTZTE254.7B-MS	4.7B	4.7	4.924	5.20	40	10	40	20	1.0	-1.7	40
PTZTE255.1B-MS	5.1B	5.1	5.368	5.70	40	8	40	20	1.5	-0.6	40
PTZTE255.6B-MS	5.6B	5.6	5.856	6.30	40	8	40	20	2.5	1.4	40
PTZTE256.2B-MS	6.2B	6.2	6.509	7.00	40	6	40	20	3.0	2.5	40
PTZTE256.8B-MS	6.8B	6.8	7.280	7.70	40	6	40	20	3.5	3.2	40
PTZTE257.5B-MS	7.5B	7.5	7.889	8.40	40	4	40	20	4.0	4.2	40
PTZTE258.2B-MS	8.2B	8.2	8.655	9.30	40	4	40	20	5.0	5.0	40
PTZTE259.1B-MS	9.1B	9.1	9.747	10.2	40	6	40	20	6.0	5.9	40
PTZTE2510B-MS	10B	10.0	10.31	11.2	40	6	40	10	7.0	6.9	40
PTZTE2511B-MS	11B	11.0	11.51	12.3	20	8	20	10	8.0	7.9	20
PTZTE2512B-MS	12B	12.0	12.50	13.5	20	8	20	10	9.0	8.7	20
PTZTE2513B-MS	13B	13.3	13.82	15.0	20	10	20	10	10.0	10.1	20
PTZTE2515B-MS	15B	14.7	15.35	16.5	20	10	20	10	11.0	11.8	20
PTZTE2516B-MS	16B	16.2	16.86	18.3	20	12	20	10	12.0	13.3	20
PTZTE2518B-MS	18B	18.0	19.00	20.3	20	12	20	10	13.0	15.0	20
PTZTE2520B-MS	20B	20.0	20.82	22.4	20	14	20	10	15.0	17.4	20
PTZTE2522B-MS	22B	22.0	23.85	24.5	10	14	10	10	17.0	19.4	10
PTZTE2524B-MS	24B	24.0	25.31	27.6	10	16	10	10	19.0	21.6	10
PTZTE2527B-MS	27B	27.0	28.70	30.8	10	16	10	10	21.0	24.6	10
PTZTE2530B-MS	30B	30.0	31.57	34.0	10	18	10	10	23.0	27.5	10
PTZTE2533B-MS	33B	33.0	34.95	37.0	10	18	10	10	25.0	30.8	10
PTZTE2536B-MS	36B	36.0	39.24	40.0	10	20	10	10	27.0	37.0	10

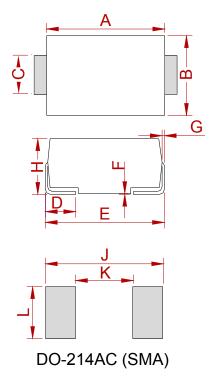
Note :

(1) The Zener Voltage  $V_Z$  is measured 40 ms after power is supplied.





#### PACKAGE MECHANICAL DATA



	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	4.25	4.65	0.167	0.183	
В	2.50	2.90	0.098	0.114	
С	1.35	1.65	0.053	0.065	
D	0.76	1.52	0.030	0.060	
E	4.93	5.28	0.194	0.208	
F	0.051	0.203	0.002	0.008	
G	0.15	0.31	0.006	0.012	
Н	1.98	2.41	0.078	0.095	
J	6.50		0.256		
к		2.30		0.090	
L	1.70		0.067		

#### **REEL SPECIFICATION**

P/N	PKG	QTY
PTZTE25XXB-MS	SMA	2000



# PTZTE25XXB-MS

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